

MDP5N50F / MDF5N50F

N-Channel MOSFET 500V, 4.5 A, 1.55Ω

MDP5N50F / MDF5N50F N-channel MOSFET 500V

General Description

The MDP5N50F/MDF5N50F use advanced Magnachip's MOSFET Technology, which provides low on-state resistance, high switching performance and excellent quality.

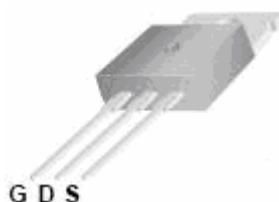
MDP5N50F/MDF5N50F are suitable device for SMPS, HID and general purpose applications.

Features

- $V_{DS} = 500V$
- $I_D = 4.5A$ @ $V_{GS} = 10V$
- $R_{DS(ON)} \leq 1.55\Omega$ @ $V_{GS} = 10V$

Applications

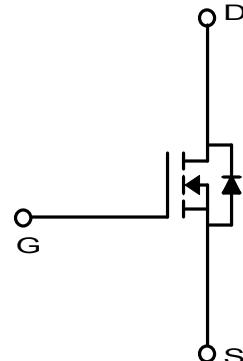
- Power Supply
- PFC
- Ballast



TO-220
MDP Series



TO-220F
MDF Series



Absolute Maximum Ratings ($T_a = 25^\circ C$)

Characteristics	Symbol	MDP5N50F	MDF5N50F	Unit
Drain-Source Voltage	V_{DSS}	500		V
Gate-Source Voltage	V_{GSS}		± 30	V
Continuous Drain Current	I_D	4.5	4.5*	A
		2.8	2.8*	A
Pulsed Drain Current ⁽¹⁾	I_{DM}	18	18*	A
Power Dissipation	P_D	93	27	W
		0.74	0.22	$W/^\circ C$
Repetitive Avalanche Energy ⁽¹⁾	E_{AR}	93		mJ
Peak Diode Recovery dv/dt ⁽³⁾	dv/dt	4.5		V/ns
Single Pulse Avalanche Energy ⁽⁴⁾	E_{AS}	230		mJ
Junction and Storage Temperature Range	T_J, T_{stg}	-55~150		°C

* I_D limited by maximum junction temperature

Thermal Characteristics

Characteristics	Symbol	MDP5N50F	MDF5N50F	Unit
Thermal Resistance, Junction-to-Ambient ⁽¹⁾	$R_{\theta JA}$	62.5	62.5	°C/W
Thermal Resistance, Junction-to-Case ⁽¹⁾	$R_{\theta JC}$	1.35	4.6	

Ordering Information

Part Number	Temp. Range	Package	Packing	RoHS Status
MDP5N50FTH	-55~150°C	TO-220	Tube	Halogen Free
MDF5N50FTH	-55~150°C	TO-220F	Tube	Halogen Free

Electrical Characteristics (Ta =25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	I _D = 250μA, V _{GS} = 0V	500	-	-	V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	2.5	-	4.5	
Drain Cut-Off Current	I _{DSS}	V _{DS} = 500V, V _{GS} = 0V	-	-	10	μA
Gate Leakage Current	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V	-	-	100	uA
Drain-Source ON Resistance	R _{Ds(ON)}	V _{GS} = 10V, I _D = 2.5A		1.25	1.55	Ω
Forward Transconductance	g _{fs}	V _{DS} = 30V, I _D = 2.5A	-	3.3	-	S
Dynamic Characteristics						
Total Gate Charge	Q _g	V _{DS} = 500V, I _D = 5.0A, V _{GS} = 10V ⁽³⁾	-	12.1	15.73	nC
Gate-Source Charge	Q _{gs}		-	3.6	-	
Gate-Drain Charge	Q _{gd}		-	4.3	-	
Input Capacitance	C _{iss}	V _{DS} = 25V, V _{GS} = 0V, f = 1.0MHz	-	500	650	pF
Reverse Transfer Capacitance	C _{rss}		-	1.5	2.25	
Output Capacitance	C _{oss}		-	65	84.5	
Turn-On Delay Time	t _{d(on)}	V _{GS} = 10V, V _{DS} = 250V, I _D = 5.0A, R _G = 25Ω ⁽³⁾	-	23	48.3	ns
Rise Time	t _r		-	30	60	
Turn-Off Delay Time	t _{d(off)}		-	37	77.7	
Fall Time	t _f		-	29	60.9	
Drain-Source Body Diode Characteristics						
Maximum Continuous Drain to Source Diode Forward Current	I _S		-	4.5	-	A
Source-Drain Diode Forward Voltage	V _{SD}	I _S = 5.0A, V _{GS} = 0V	-		1.4	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = 5.0A, dI/dt = 100A/μs ⁽³⁾	-	80		ns
Body Diode Reverse Recovery Charge	Q _{rr}		-	1.6		μC

Note :

1. Pulse width is based on R_{θJC} & R_{θJA} and the maximum allowed junction temperature of 150°C.
2. Pulse test: pulse width ≤300us, duty cycle≤2%, pulse width limited by junction temperature TJ(MAX)=150°C.
3. I_{SD} ≤4.5A, di/dt≤200A/us, V_{DD}=50V, R_g =25Ω, Starting TJ=25°C
4. L=20.5mH, I_{AS}=4.5A, V_{DD}=50V, , R_g =25Ω, Starting TJ=25°C

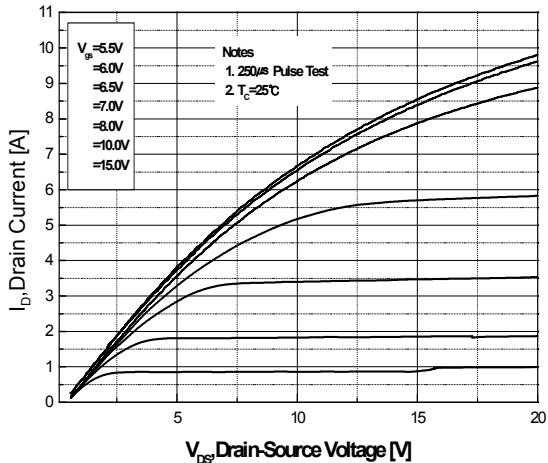


Fig.1 On-Region Characteristics

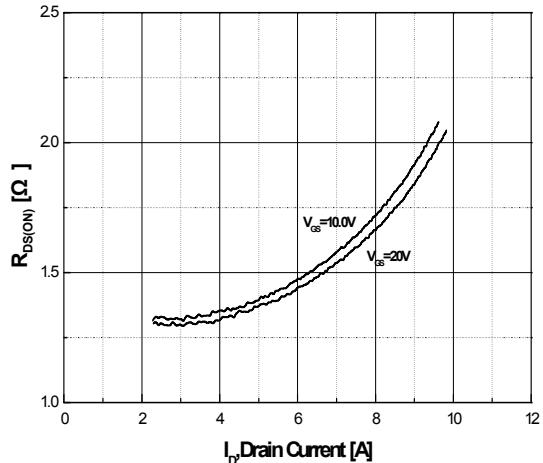


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

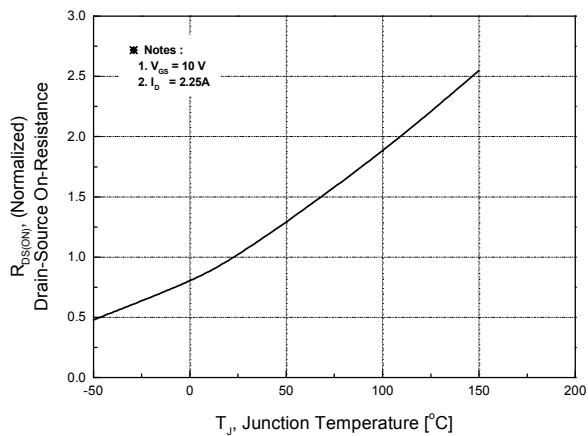


Fig.3 On-Resistance Variation with Temperature

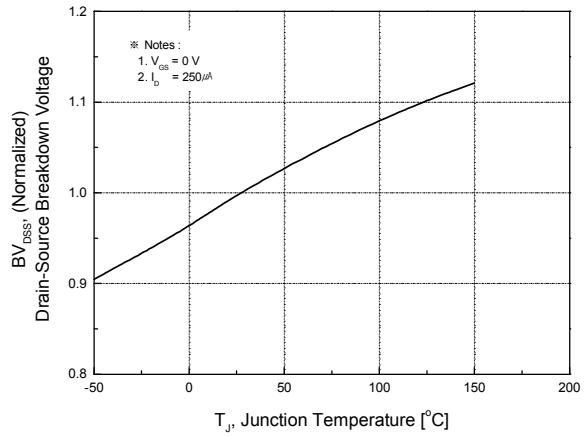


Fig.4 Breakdown Voltage Variation vs. Temperature

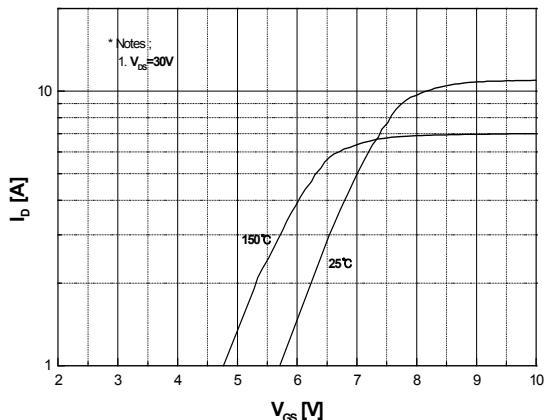


Fig.5 Transfer Characteristics

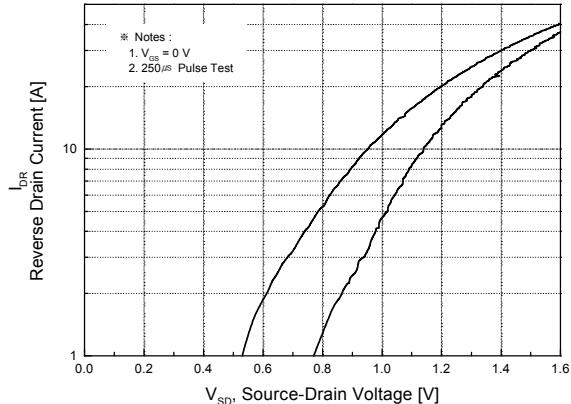


Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature

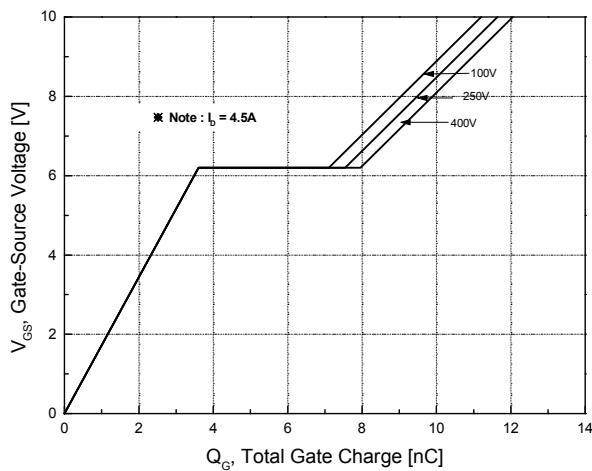


Fig.7 Gate Charge Characteristics

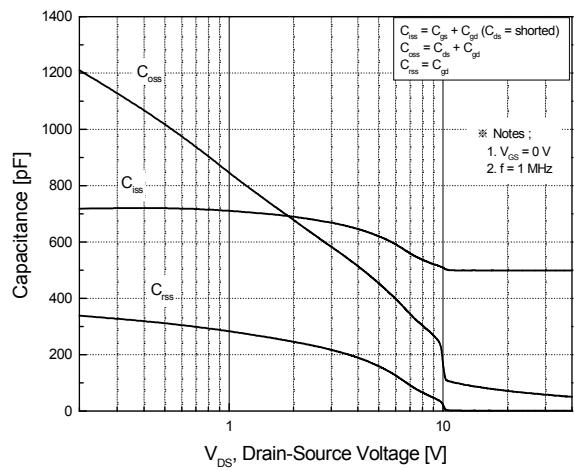
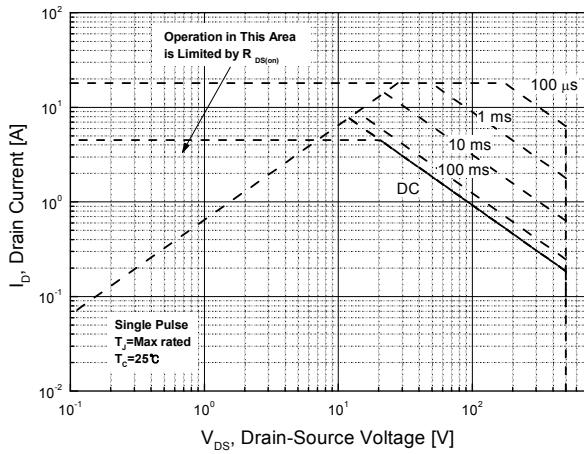


Fig.8 Capacitance Characteristics



**Fig.9 Maximum Safe Operating Area
MDP5N50F (TO-220)**

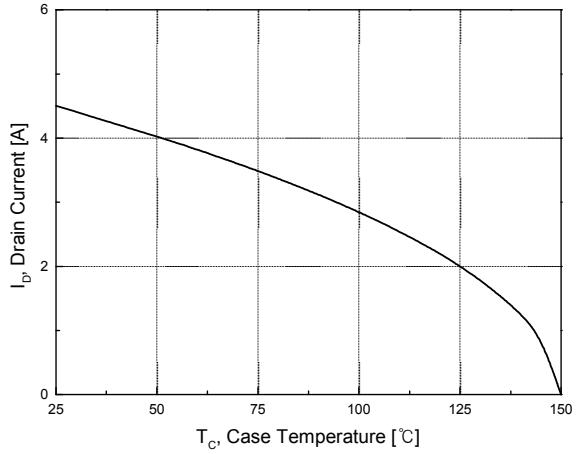
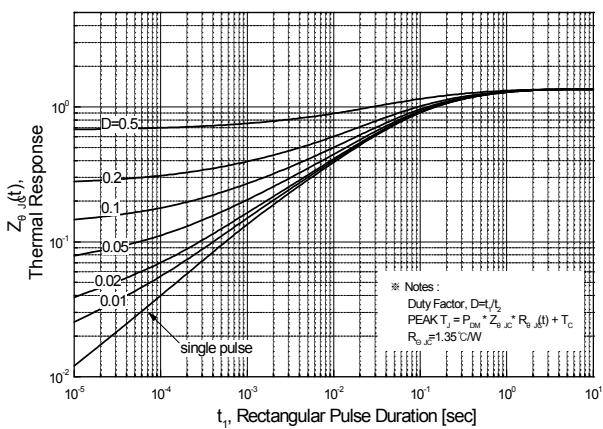


Fig.10 Maximum Drain Current vs. Case Temperature



**Fig.11 Transient Thermal Response Curve
MDP5N50F (TO-220)**

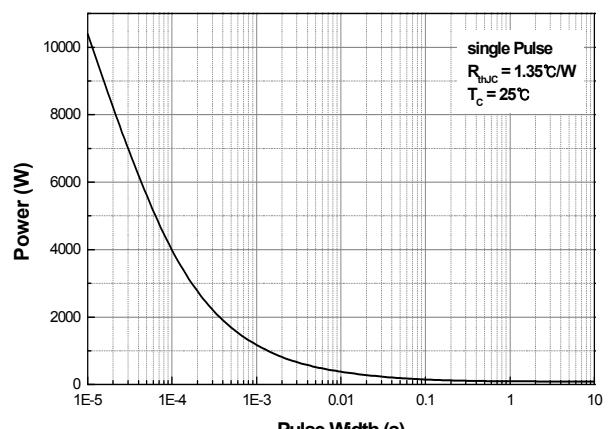
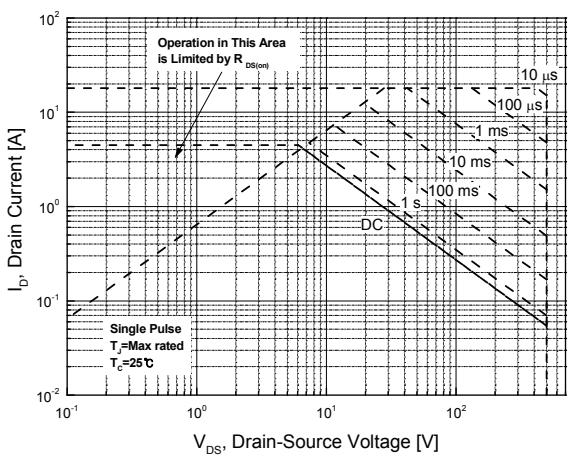
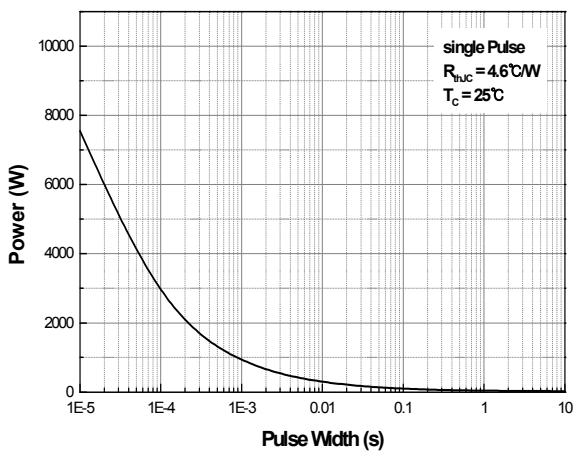


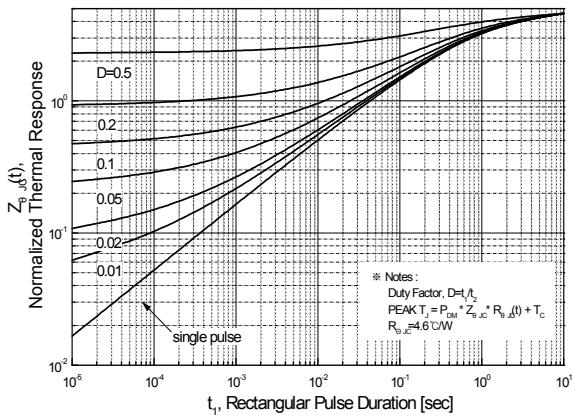
Fig.12 Single Pulse Maximum Power Dissipation – MDP5N50F (TO-220)



**Fig.13 Maximum Safe Operating Area
MDF5N50F (TO-220F)**



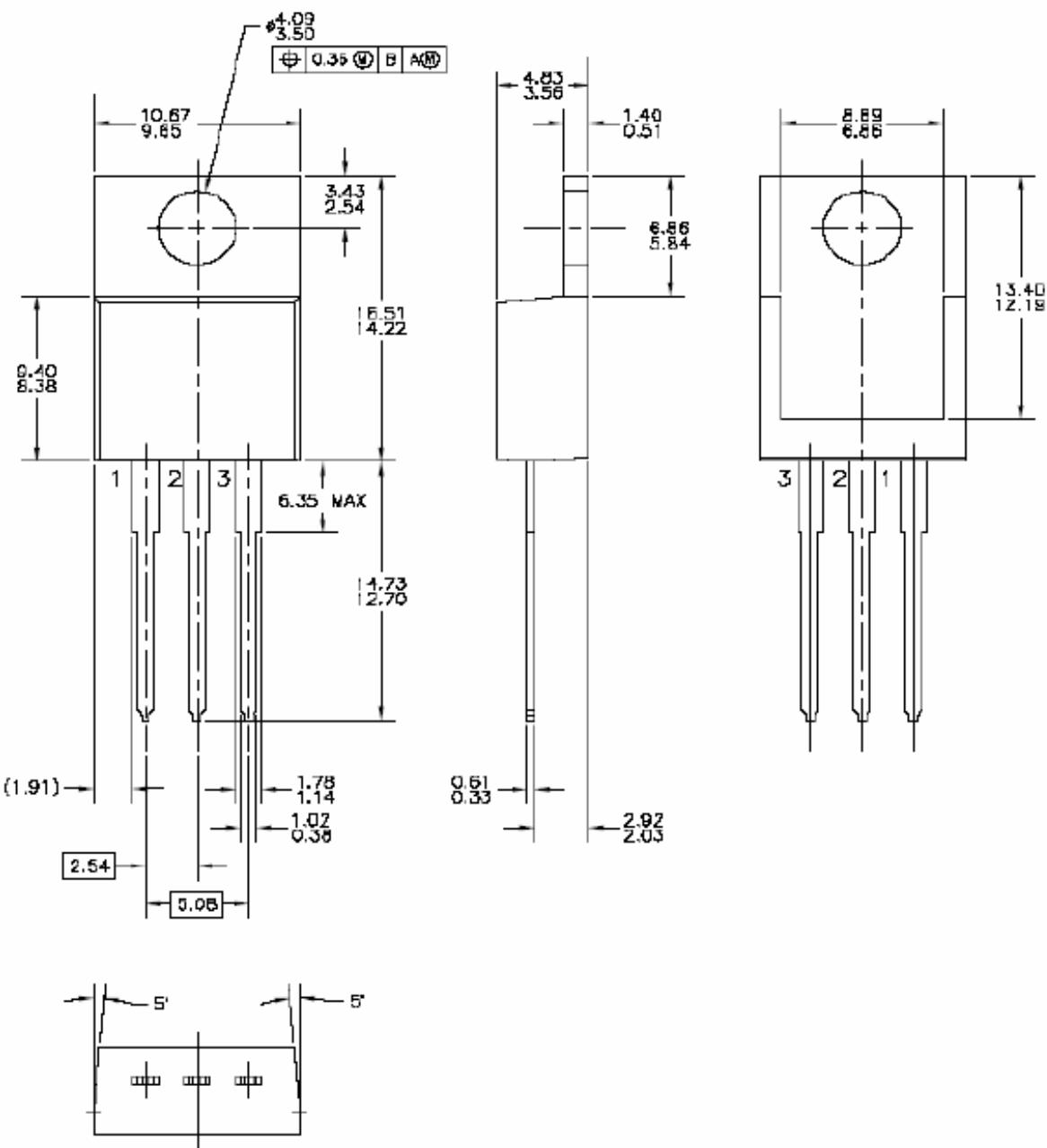
**Fig.12 Single Pulse Maximum Power
Dissipation- MDF5N50F (TO-220F)**



**Fig.11 Transient Thermal Response Curve
MDF5N50F (TO-220F)**

Physical Dimensions

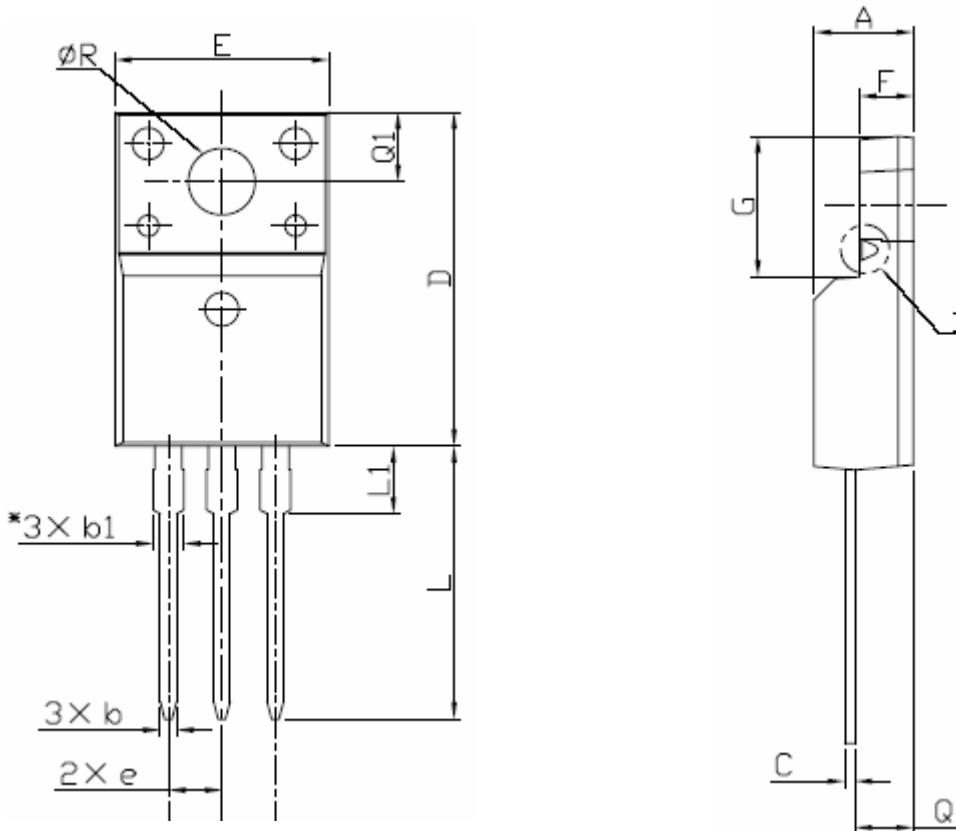
TO-220



Physical Dimensions

3 Leads, TO-220F

Dimensions are in millimeters unless otherwise specified



Symbol	Min	Nom	Max
A	4.50		4.93
b	0.63		0.91
b1	1.15		1.47
C	0.33		0.63
D	15.47		16.13
E	9.60		10.71
e		2.54	
F	2.34		2.84
G	6.48		6.90
L	12.24		13.72
L1	2.79		3.67
Q	2.52		2.96
Q1	3.10		3.50
ØR	3.00		3.55